



AO3400

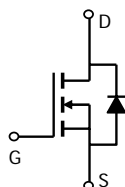
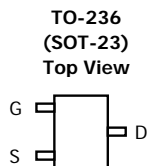
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO3400 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO3400 is Pb-free (meets ROHS & Sony 259 specifications). AO3400L is a Green Product ordering option. AO3400 and AO3400L are electrically identical.*

Features

$V_{DS} (V) = 30V$
 $I_D = 5.8 A (V_{GS} = 10V)$
 $R_{DS(ON)} < 28m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 33m\Omega (V_{GS} = 4.5V)$
 $R_{DS(ON)} < 52m\Omega (V_{GS} = 2.5V)$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	I_D	5.8	A
$T_A=25^\circ C$		4.9	
Pulsed Drain Current ^B	I_{DM}	30	
Power Dissipation ^A	P_D	1.4	W
		$T_A=25^\circ C$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	65	90	$^\circ C/W$
$t \leq 10s$		85	125	
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	43	60	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.7	1.1	1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=5.8\text{A}$ $T_J=125^\circ\text{C}$		22.8	28	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=5\text{A}$		27.3	33	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$, $I_D=4\text{A}$		43.3	52	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=5\text{A}$	10	15		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.71	1	V
I_S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance			823	1030	pF
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		99		pF
C_{rss}	Reverse Transfer Capacitance			77		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.2	3.6	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge			9.7	12	nC
Q_{gs}	Gate Source Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=15\text{V}$, $I_D=5.8\text{A}$		1.6		nC
Q_{gd}	Gate Drain Charge			3.1		nC
$t_{D(on)}$	Turn-On Delay Time			3.3	5	ns
t_r	Turn-On Rise Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=2.7\Omega$,		4.8	7	ns
$t_{D(off)}$	Turn-Off Delay Time	$R_{GEN}=3\Omega$		26.3	40	ns
t_f	Turn-Off Fall Time			4.1	6	ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		16	20	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		8.9	12	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $\leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using $80\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

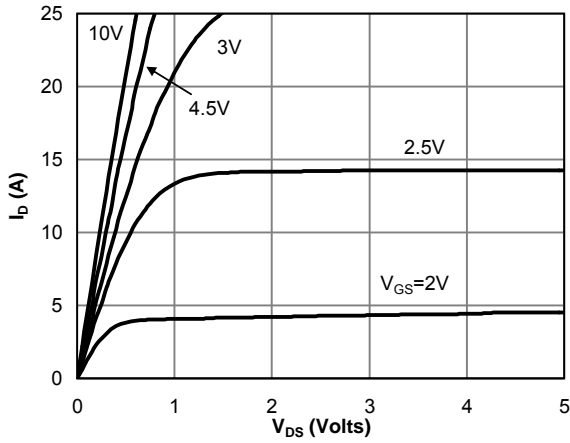


Fig 1: On-Region Characteristics

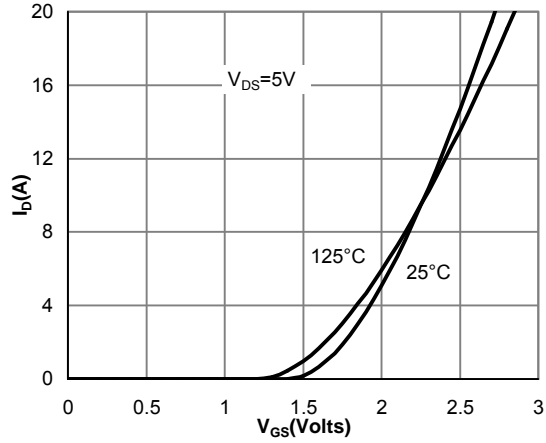


Figure 2: Transfer Characteristics

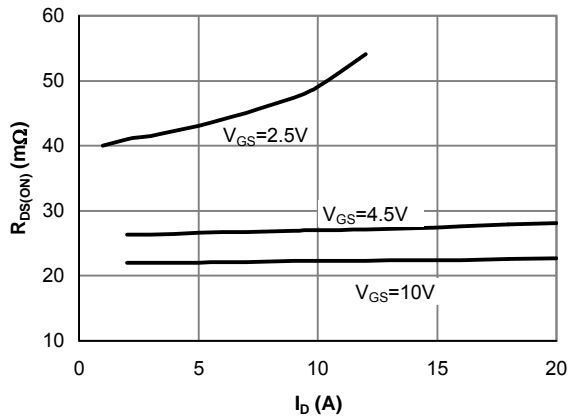


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

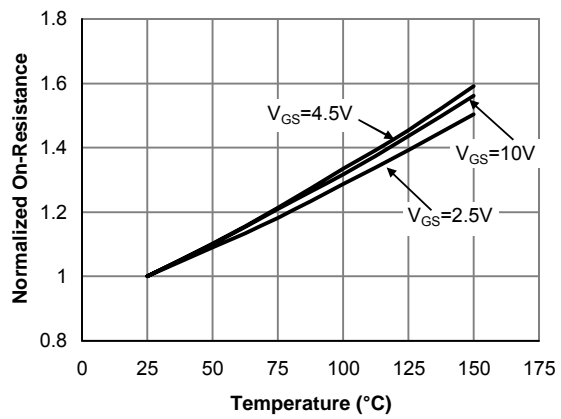


Figure 4: On-Resistance vs. Junction Temperature

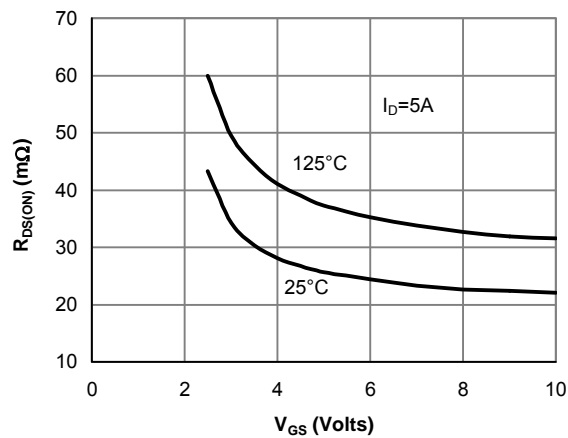


Figure 5: On-Resistance vs. Gate-Source Voltage

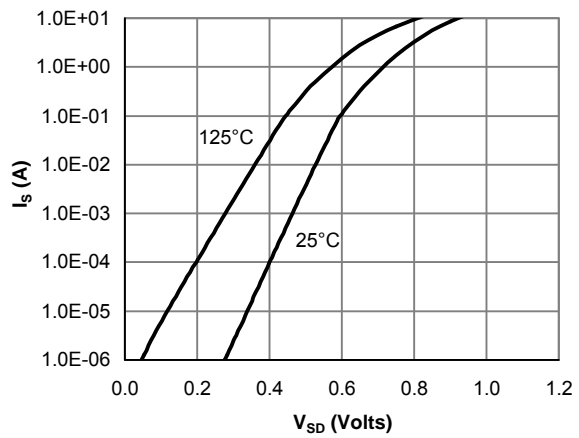


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

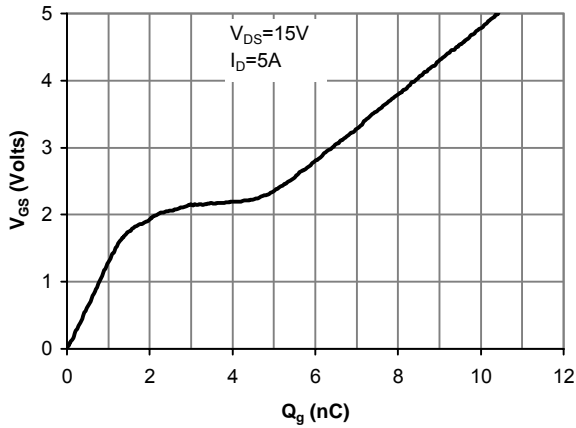


Figure 7: Gate-Charge Characteristics

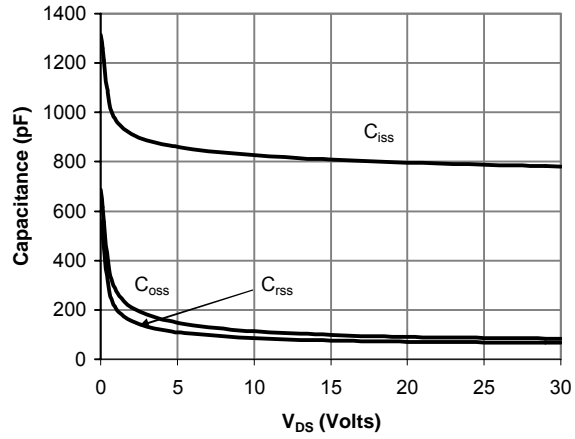


Figure 8: Capacitance Characteristics

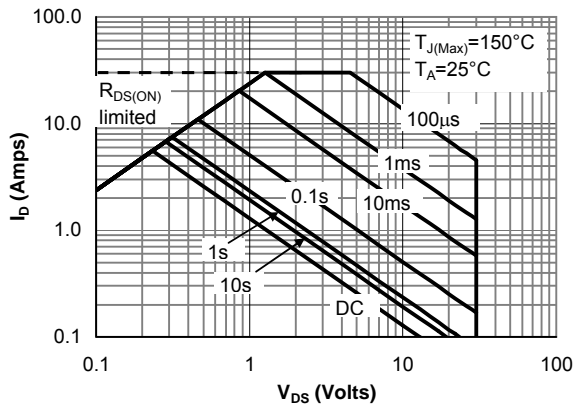


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

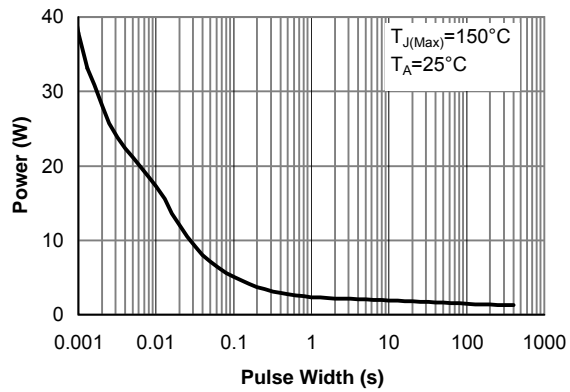


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

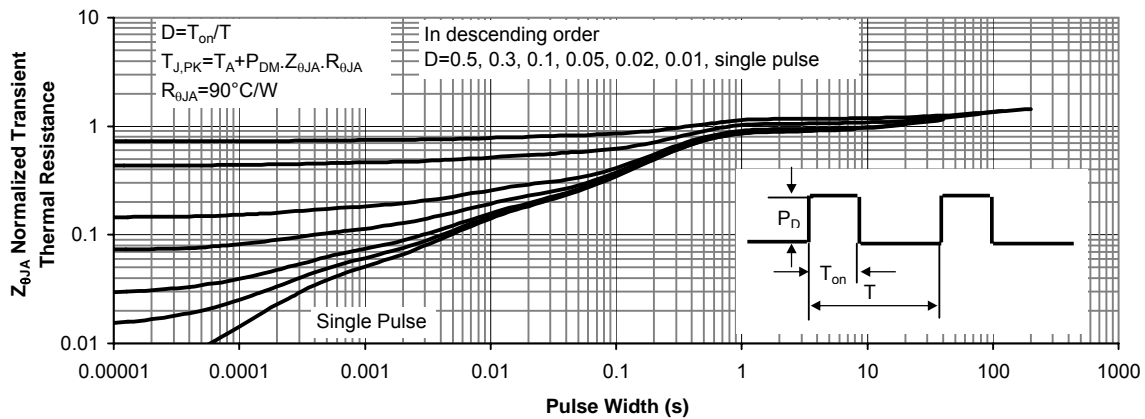


Figure 11: Normalized Maximum Transient Thermal Impedance